HARRIS

RFM8P08/8P10
RFP8P08/8P10

P-Channel Enhancement-Mode Power Field-Effect Transistors

August 1991

Features

- -8A, -80V and -100V
- $r_{DS(on)} = 0.4\Omega$
- SOA is Power-Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device

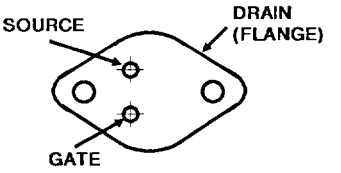
Description

The RFM8P08 and RFM8P10 and the RFP8P08 and RFP8P10 are p-channel enhancement-mode silicon gate power field-effect transistors designed for applications such as switching regulators, switching converters, relay drivers, and drivers for high-power bipolar switching transistors requiring high speed and low gate-drive power. These types can be operated directly from integrated circuits.

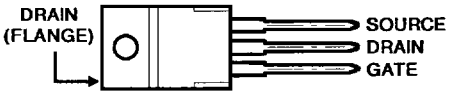
The RFM series types are supplied in the JEDEC TO-204AA steel package and the RFP series types in the JEDEC TO-220AB plastic package.

Packages

TO-204AA
BOTTOM VIEW

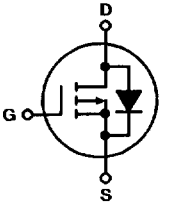


TO-220AB
TOP VIEW



Terminal Diagram

P-CHANNEL ENHANCEMENT MODE



Absolute Maximum Ratings ($T_C = 25^oC$) Unless Otherwise Specified

	RFM8P08	RFM8P10	RFP8P08	RFP8P10	UNITS
Drain-Source Voltage ..... V_{DS}	-80	-100	-80	-100	V
Drain-Gate Voltage ($R_{GS} = 1m\Omega$) ..... V_{DGR}	-80	-100	-80	-100	V
Continuous Drain Current					
RMS Continuous ..... I_D	8	8	8	8	A
Pulsed Drain Current ..... I_{DM}	20	20	20	20	A
Gate-Source Voltage ..... V_{GS}	±20	±20	±20	±20	V
Maximum Power Dissipation					
$T_C = +25^oC$ ..... P_D	100	100	75	75	W
Above $T_C = +25^oC$, Derate Linearly	0.8	0.8	0.6	0.6	W/^{o}C
Operating and Storage Junction ..... T_J, T_{STG} Temperature Range	-55 to +150	-55 to +150	-55 to +150	-55 to +150	^{o}C

CAUTION: These devices are sensitive to electrostatic discharge. Proper I.C. handling procedures should be followed.

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File Number **1496**

ELECTRICAL CHARACTERISTICS, *At Case Temperature (T_C)=25° C unless otherwise specified.*

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	LIMITS				UNITS
			RFM8P08 RFP8P08		RFM8P10 RFP8P10		
			MIN.	MAX.	MIN.	MAX.	
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=1 mA V_{GS}=0	-80	—	-100	—	V
Gate Threshold Voltage	$V_{GS}(th)$	V_{GS}=V_{DS} I_D=1 mA	-2	-4	-2	-4	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-65 V V_{DS}=-80 V	— —	1 —	— —	— 1	μA
		T_C=125° C V_{DS}=-65 V V_{DS}=-80 V	— —	50 —	— —	— 50	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20 V V_{DS}=0	—	100	—	100	nA
Drain-Source On Voltage	$V_{DS}(on)$[a]	I_D=4 A V_{GS}=-10 V	—	-1.6	—	-1.6	V
		I_D=8 A V_{GS}=-10 V	—	-4.0	—	-4.0	V
Static Drain-Source On Resistance	$r_{DS}(on)$[a]	I_D=4 A V_{GS}=-10 V	—	.4	—	.4	Ω
Forward Transconductance	g_{fs}[a]	V_{DS}=-10 V I_D=4 A	2	—	2	—	mho
Input Capacitance	C_{iss}	V_{DS}=25 V V_{GS}=0 V f = 1MHz	—	1500	—	1500	pF
Output Capacitance	C_{oss}		—	700	—	700	pF
Reverse Transfer Capacitance	C_{rss}		—	300	—	300	pF
Turn-On Delay Time	$t_d(on)$	V_{DD} = 50 V I_D=4 A R_{gen}=R_{gs}=50 Ω V_{GS}=-10 V	18(typ)	60	18(typ)	60	ns
Rise Time	t_r		70(typ)	150	70(typ)	150	ns
Turn-Off Delay Time	$t_d(off)$		166(typ)	275	166(typ)	275	ns
Fall Time	t_f		94(typ)	175	94(typ)	175	ns
Thermal Resistance Junction-to-Case	$R\theta_{JC}$	RFM8P08, RFM8P10	—	1.25	—	1.25	°C/W
		RFP8P08, RFP8P10	—	1.67	—	1.67	°C/W

[a]Pulsed: Pulse duration = 300 μs max., duty cycle = 2%.

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS				UNITS
			RFM8P08 RFP8P08		RFM8P10 RFP8P10		
			Min.	Max.	Min.	Max.	
Diode Forward Voltage	V_{SD}	I_{SD} = 4A	—	1.4	—	1.4	V
Reverse Recovery Time	t_{rr}	I_F = 4A d_{IF}/d_t = 100A/μs	200(typ.)		200(typ.)		ns

*Pulse Test: Width ≤ 300 μs, Duty Cycle ≤ 2%.

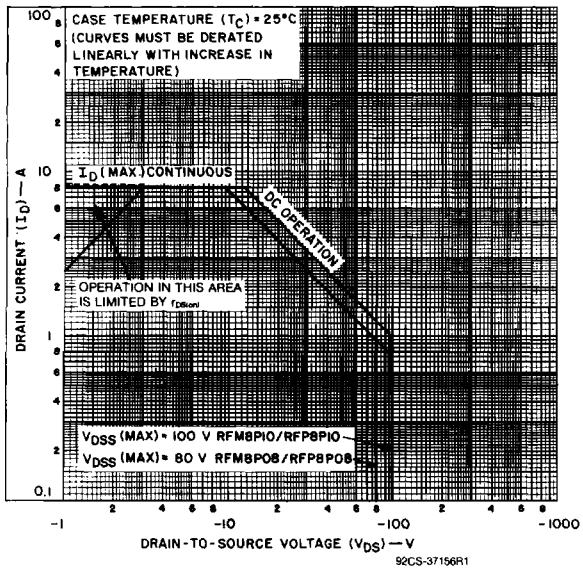

Fig. 1 — Maximum operating areas for all types.

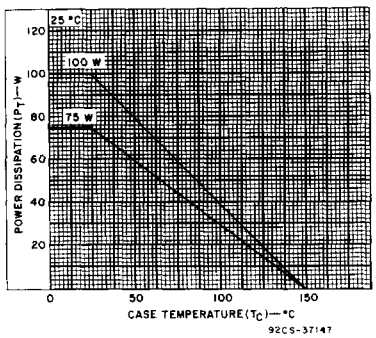

Fig. 2 — Power dissipation vs. case temperature derating curve for all types.

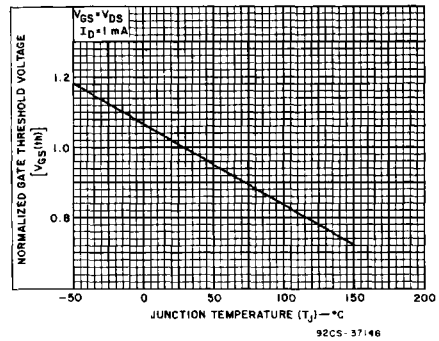

Fig. 3 — Typical normalized gate threshold voltage as a function of junction temperature for all types.

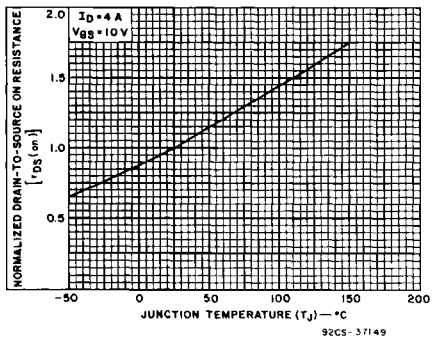

Fig. 4 — Normalized drain-to-source on resistance to junction temperature for all types.

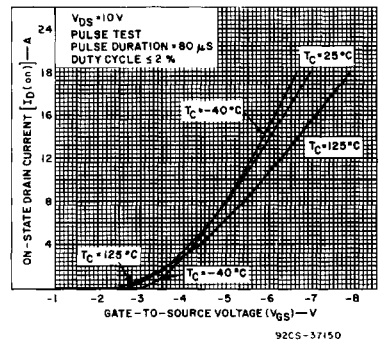

Fig. 5 — Typical transfer characteristics for all types.

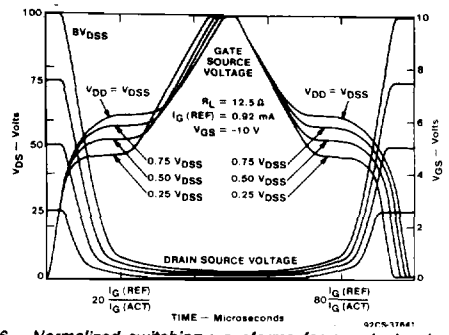

Fig. 6 - Normalized switching waveforms for constant gate-current. Refer to Harris application notes AN-7254 and AN-7260.

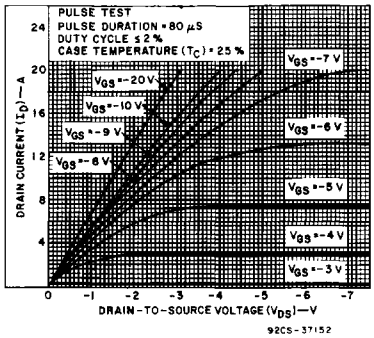

Fig. 7 — Typical saturation characteristics for all types.

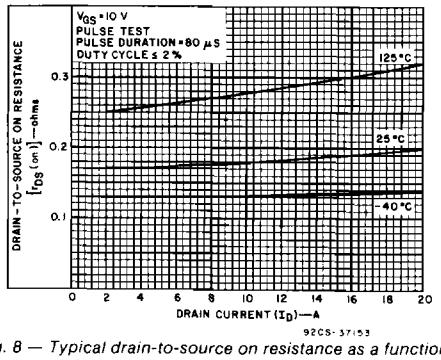

Fig. 8 — Typical drain-to-source on resistance as a function of drain current for all types.

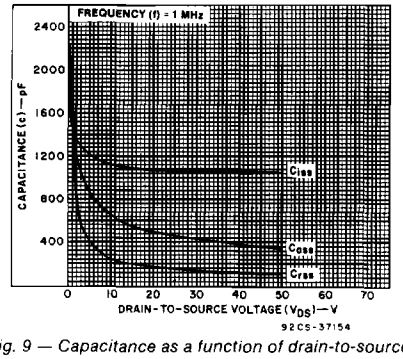

Fig. 9 — Capacitance as a function of drain-to-source voltage for all types.

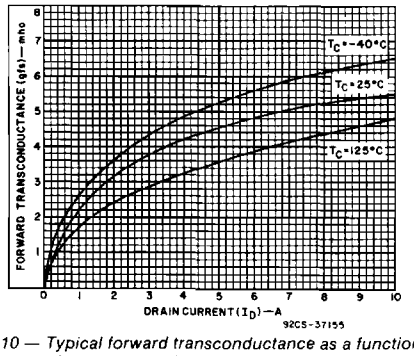

Fig. 10 — Typical forward transconductance as a function of drain current for all types.

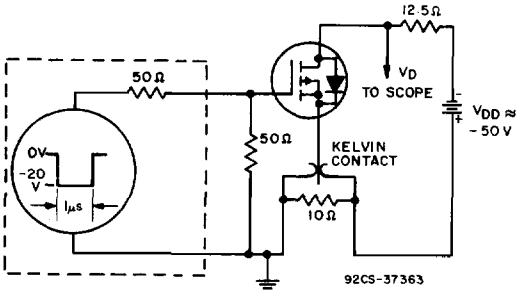

Fig. 11 — Switching Time Test Circuit.